

Micron's IBIS Model Quality Process

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Overview

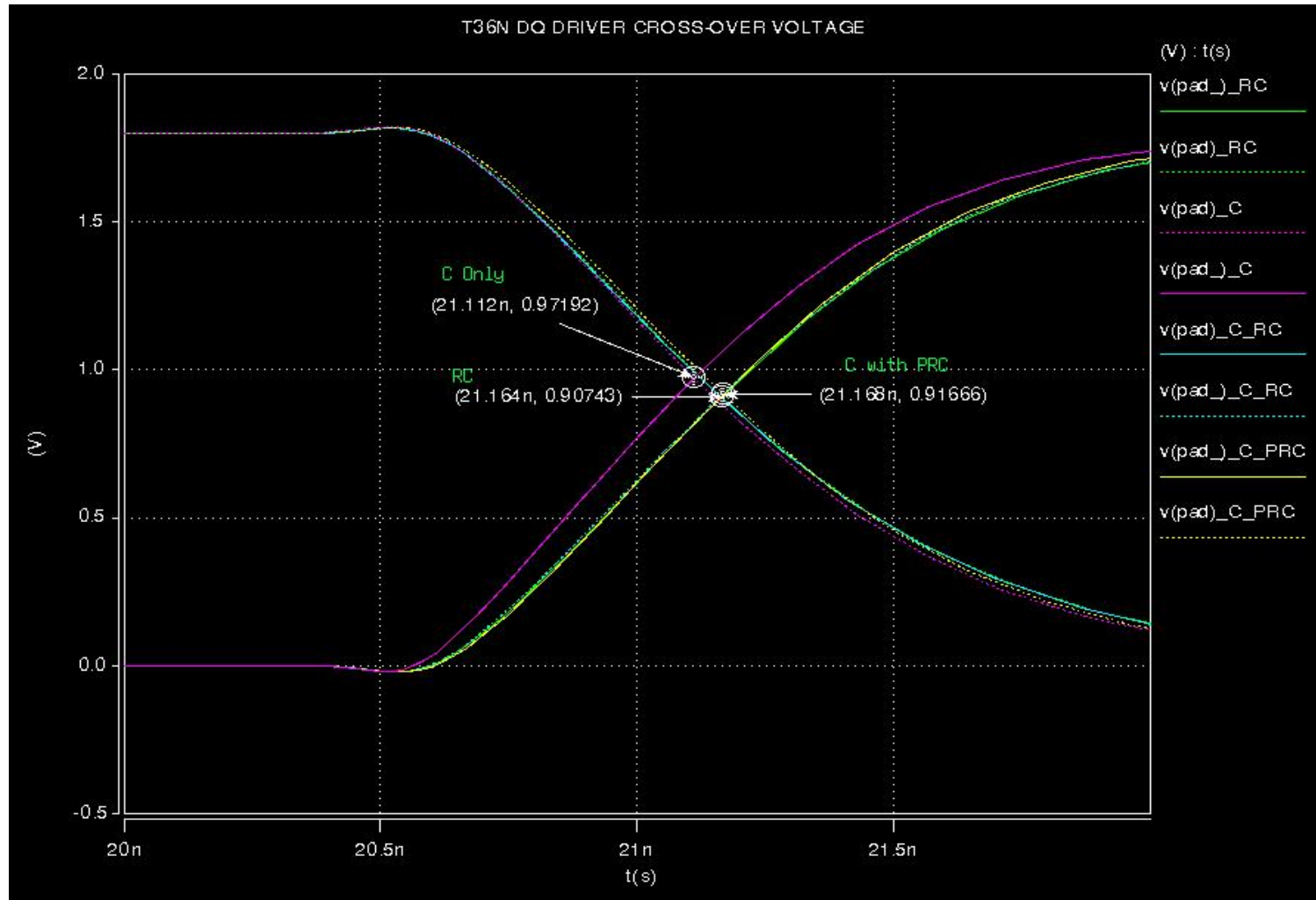
- Micron builds in quality checks into each step of the model creation process
 - Spice netlist creation
 - IBIS creation process
- Quality Report documentation for customers
- Conclusions

Spice netlist creation

- Multiple pre-driver stages are included - critical timing paths unmodified
- Standard Parasitic Format (SPF) netlists are created for circuits with completed layouts
- SPF includes two flavors
 - C only – Capacitance of all layout structures included
 - RC – Resistance and Capacitance included
 - RC is more accurate but creates unreasonably large netlists
 - C only with additional PRC elements on critical nets can approach accuracy of RC netlist but be much smaller

Spice Netlist: SPF Format Effect on Vox

In this example, PRC elements were needed to properly model the effect of long, imbalanced metal lines between the pre-driver logic and pre-driver stages.

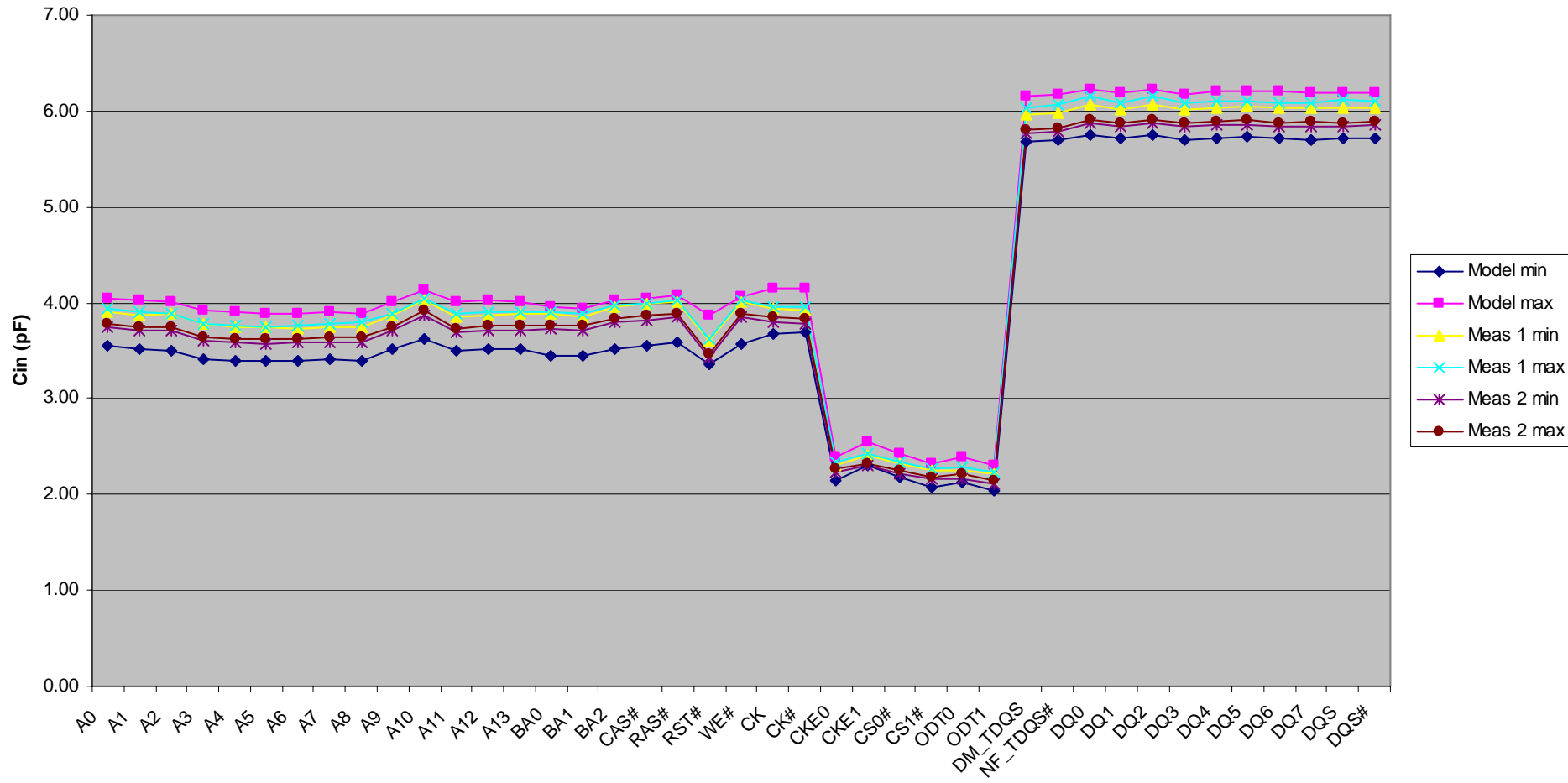


Quality ☒: Correct Vox level

Determining C_comp min/max

$$C_{\text{model_min}} = C_{\text{package}} + C_{\text{comp_min}}$$

$$C_{\text{model_max}} = C_{\text{package}} + C_{\text{comp_max}}$$



Quality ☒: Correct C_package and C_comp

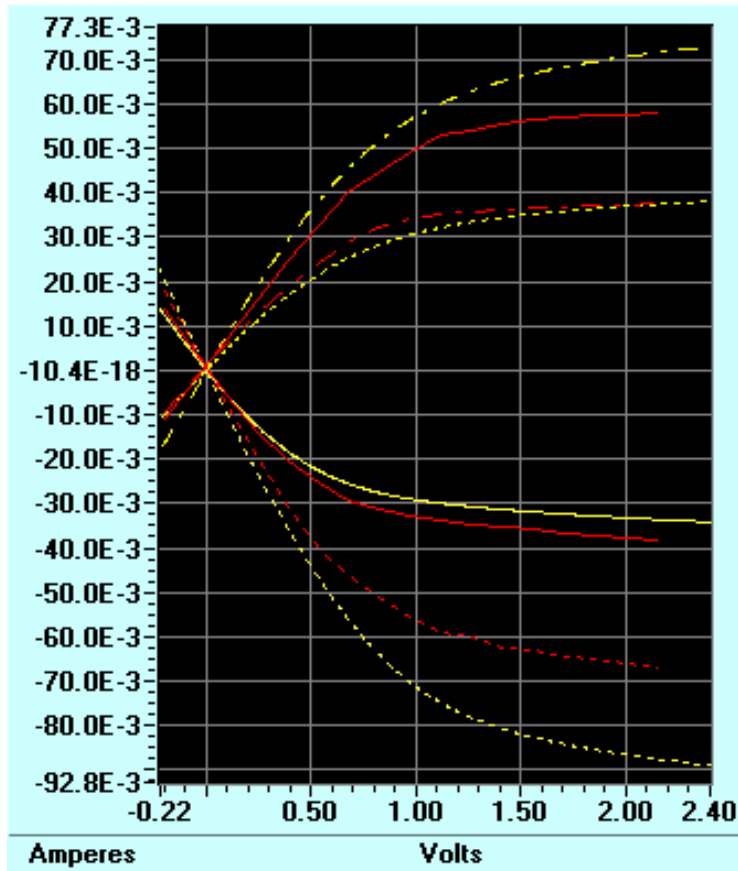
Correlating I-V curves to Measurements

- Must match exact Process/Voltage/Temp conditions between Spice simulation and Measurement
- Process model adjustment example
 - Process corners set by parameter range: -1=Slow, 0=Typical, 1=Fast
 - IDSN model corners ($\mu\text{A}/\mu\text{m}$) (for specific V_{ds} and V_{gs} voltage setting)
Slow: 359.0 Typical: 399.8 Fast: 450.9
Silicon Measurement: 397.3, Adjusted 6.1% towards Slow (-0.061)
 - IDSP model corners ($\mu\text{A}/\mu\text{m}$)
Slow: 173.1 Typical: 203.7 Fast: 242.1
Silicon Measurement: 194.1 , Adjusted 31.5% towards Slow (-0.315)

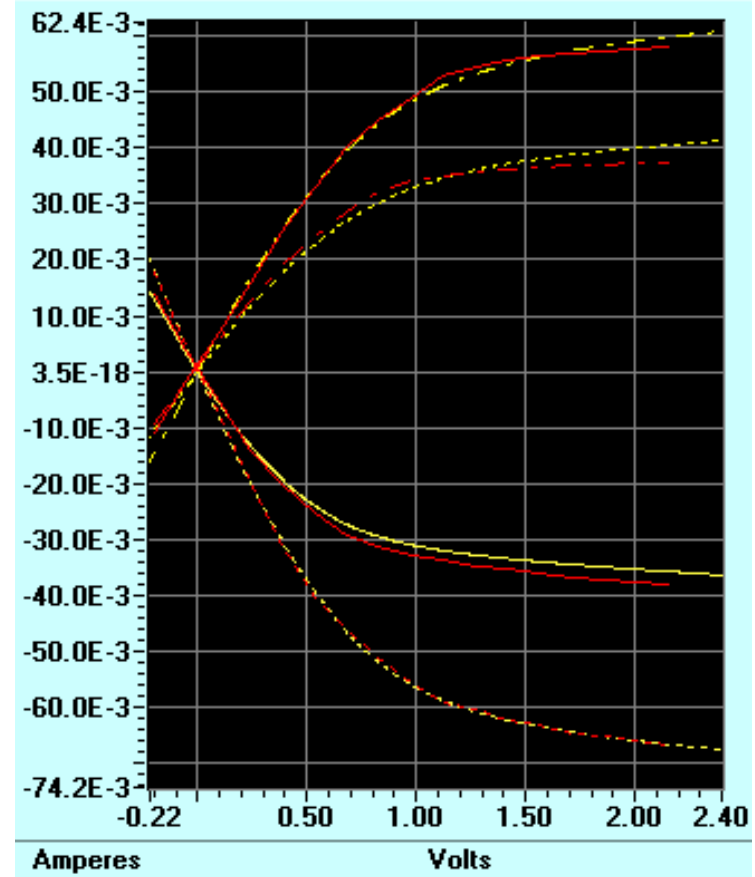
Correlating I-V curves to Measurements

- Model = yellow, Measurement = red

Before PVT Adjustment



After PVT Adjustment



Quality ☒: I-V curves match measurements

Model Quality

- Model Creation Checklists

- Spice model development

- ✓: Transistor model libraries setup and correlated to speed grades

- ✓: Correct power supply decoupling included in netlists

- ✓: Variable capacitance added to PAD node for proper C_comp variation

- ✓: Clamp diode currents adjusted through bulk node resistance

- ✓: All control signal combinations function properly

Model Quality

- Model Creation Checklists

- IBIS model development

- ✓: Run IBISCHK – explain any warnings

- ✓: Component names and Pin lists agree with the datasheet

- ✓: Input model parameters match the datasheet

- ✓: I/O model parameters match the datasheet

- ✓: V-t curves time correlated and on/off time relationships valid

- ✓: Combined Submodel curves show proper ODT voltage midpoint termination and resistance

Quality Reports

- IBIS Open Forum – IBIS Quality Task Group
 - Released the IBIS Quality Specification, Rev 1.0, 3/31/04
 - Currently working on an updated release
- Micron follows the IQ Spec, but releases a detailed report with each model
 - Compares model to specification data
 - Compares model to measurement data
 - Compares IBIS model to HSPICE model

Quality Reports - Introduction

IBIS/HSPICE Model Quality Report

Design ID: **T35M**

Description: **128Mb Mobile DDR SDRAM**

Marketing device name(s): **MT46H8M16LFBF, MT46H4M32LFB5, MT46H8M16LFT35M, MT46H4M32LFT35M**

Valid Speed Grades: **-75 (266), -6 (333), -54 (370), -5 (400)**

Zip File Name: **t35m_ibis.zip, t35m_it_ibis.zip**

IBIS File name: **t35m.ibs, t35m_it.ibs** File rev: **2.0, 2.0**

HSPICE File name: **t35m_hspice.zip** File rev: **2.0**

EBD file name (if applicable): File rev:

Die Rev: **K**

Date: **October 8, 2008**

Datasheet Link:

http://download.micron.com/pdf/datasheets/dram/mobile/128mb_mobile_ddr_sdram_t35m.pdf

E-mail at modelsupport@micron.com for questions regarding Quality Report

Device Parameters

VDDQ – Slow: **1.70** Typical: **1.80** Fast: **1.95**

VDD – Slow: **1.70** Typical: **1.80** Fast: **1.95**

Junction Temperature (Commercial) - Slow: **85** Typical: **40** Fast: **0**

Junction Temperature (Industrial) - Slow: **100** Typical: **40** Fast: **-40**

VDDQ/VSSQ Decoupling Capacitance: **2.76nF**

Included in HSPICE DQ/DQS models? **yes** Amount per DQ/DQS model: **76.66pF**

VDDQ/VSSQ Decoupling Capacitance Series Resistance: **1 ohm**

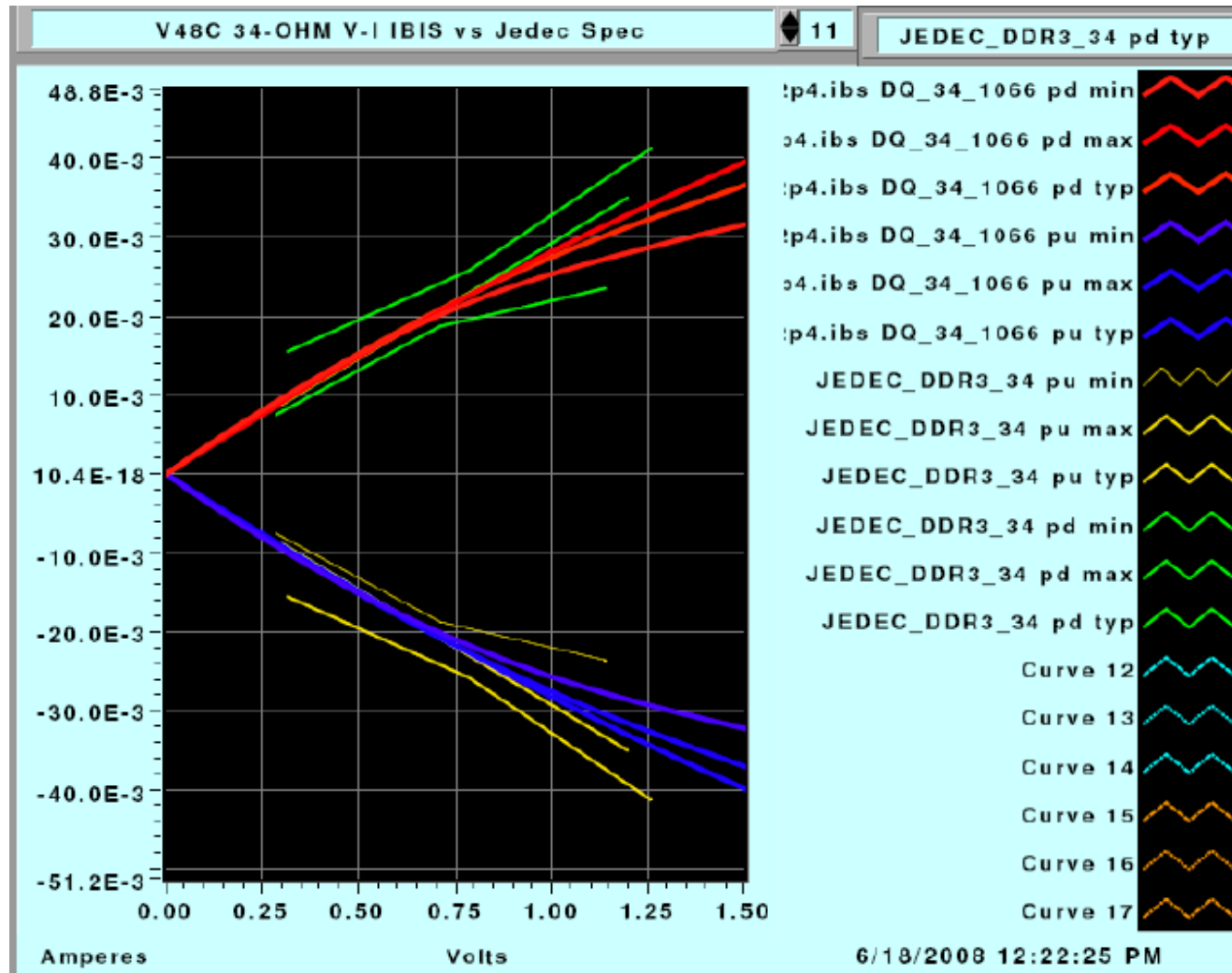
Quality Reports – IQ Summary

- IBIS Quality Summary included based on IQ 1.0 specification
- Report will detail IQ 1.1 spec once released
- IBIS model does not include full IQ Summary, but instead states:

| IQ SUMMARY Overall Quality of component and models Level 2b

| See Micron IBIS Model Quality Report for full IQ SUMMARY

Quality Reports – IOH/IOL vs. Spec



Quality Reports – C_comp, ODT & Slew Rates vs. Specification

C_comp

		IBIS		Datasheet (DDR3-1600)	
		Min	max	min	max
DQ	C_comp	1.55pF	1.94pF		
	C_package	0.20pF	0.26pF		
	C_total	1.75pF	2.2pF	1.5pF	2.3pF
INPUT	C_comp	0.6pF	0.91pF		
	C_package	0.17pF	0.36pF		
	C_total	0.77pF	1.27pF	0.75pF	1.3pF
CLK	C_comp	0.76pF	0.99pF		
	C_package	0.20pF	0.21pF		
	C_total	0.96pF	1.20pF	0.8pF	1.4pF

ODT

	TYP	MIN	MAX
V _{inl} (V)	0.575	0.5375	0.6125
V _{inh} (V)	0.925	0.8875	0.9625
I _{inl} (A)	-0.0073	-0.0068	-0.00793
I _{inh} (A)	0.007425	0.00615	0.00789
R _{tt} (Model)	23.77	22.12	27.03
R _{tt} (datasheet-in units of ZQ/12)	1.00	0.90	1.60
R _{tt} (datasheet)	20.00	18.00	32.00

Slew Rates

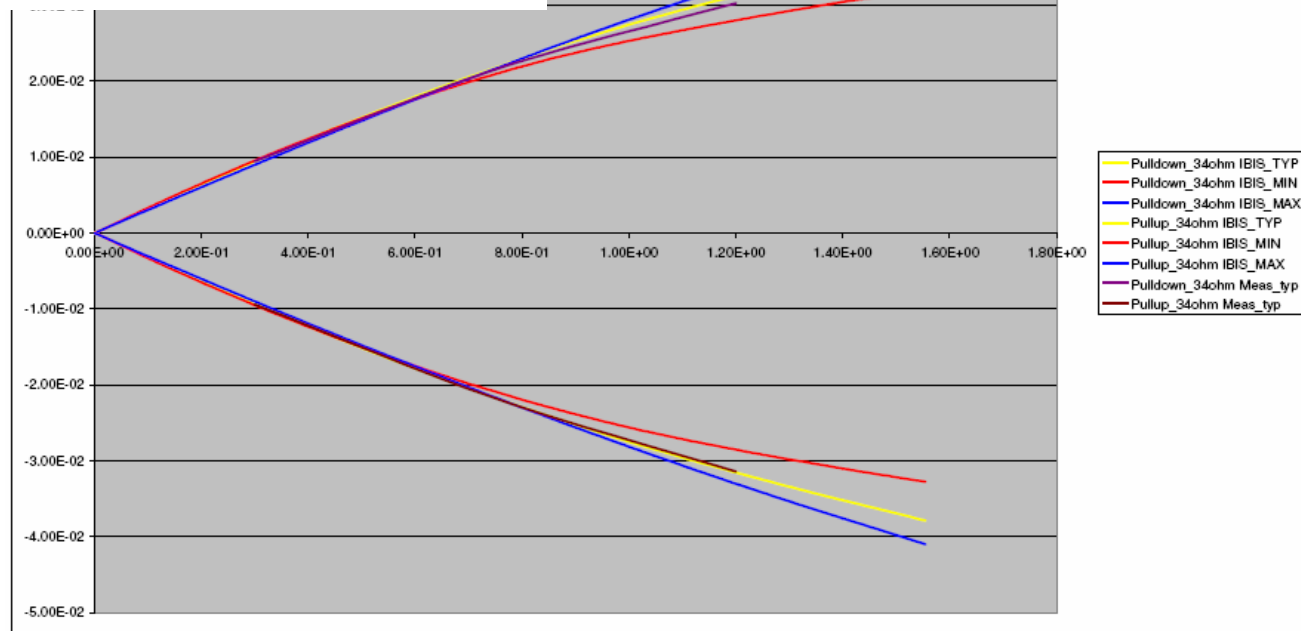
		Simulation			Datasheet	
Model	Slew Rate (V/ns)	min	Typ	max	min	max
DQ_34_1066	Rising	2.27	2.84	3.88	2.5	5
	Falling	3.24	4.03	5.17	2.5	5
DQ_34_1333	Rising	3.15	3.25	4.31	3	5
	Falling	4.72	4.9	6.63	3	5
DQ_34_1600	Rising	3.83	3.87	3.92	3	5
	Falling	4.25	4.45	6	3	5

Quality Reports – C_comp & IOH/IOL vs. Measurement

C_comp

		IBIS			Measured		
		Min	Typ	max	min	typ	max
DQ	C_comp	1.55pF	1.72pF	1.94pF	NA	NA	NA
	C_package	0.20pF	0.22pF	0.26pF	NA	NA	NA
	C_total	1.75pF	2.02pF	2.2pF	1.90pF	2.01pF	2.20pF
INPUT	C_comp	0.6pF	0.77pF	0.91pF	NA	NA	NA
	C_package	0.17pF	0.25pF	0.36pF	NA	NA	NA
	C_total	0.77pF	1.31pF	1.27pF	0.96pF	1.09pF	1.28pF
CLK	C_comp	0.76pF	0.87pF	0.99pF	NA	NA	NA
	C_package	0.20pF	0.21pF	0.21pF	NA	NA	NA
	C_total	0.96pF	1.29pF	1.20pF	1.13pF	1.16pF	1.18pF

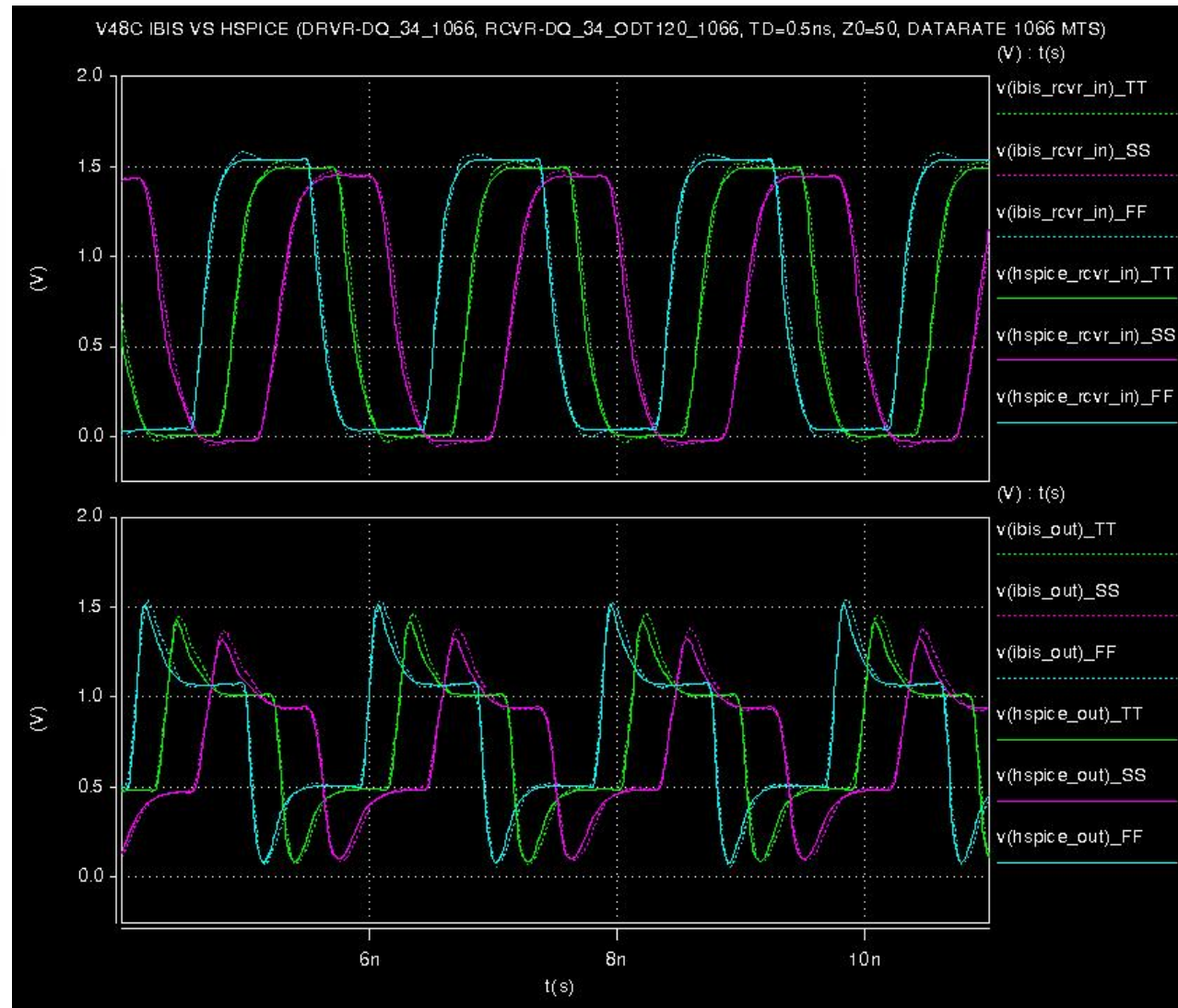
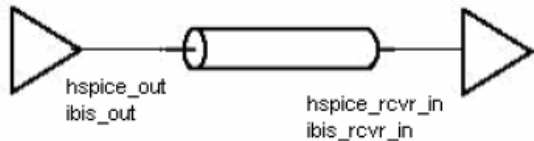
IOH/IOL



Quality Reports – IBIS vs. HSPICE

Test load

T-line: Z0 50 ohms,
Td=0.5ns



Conclusions

- Model users demand quality models
- IBIS Quality Committee work is essential for standardizing quality levels and methods
- IBIS Quality checklists work to maintain quality standards
- Quality Reports go above and beyond checklists to document thorough model checking
- Demand Quality models from vendors!
 - Show them examples of quality models.

